DISCRETE SEMICONDUCTORS

DATA SHEET

PEMB2; PUMB2 PNP/PNP resistor-equipped transistors; R1 = 47 kΩ, R2 = 47 kΩ

Product data sheet Supersedes data of 2001 Sep 14

2003 Oct 15



PNP/PNP resistor-equipped transistors; R1 = 47 k Ω , R2 = 47 k Ω

PEMB2; PUMB2

MAX.

UNIT

TYP.

FEATURES

- Built-in bias resistors
- · Simplified circuit design
- · Reduction of component count
- · Reduced pick and place costs.

APPLICATIONS

- · Low current peripheral drivers
- Replacement of general purpose transistors in digital applications
- · Control of IC inputs.

V_{CEO}	collector-emitter voltage	_	-50	V
I _O	output current (DC)	-	-100	mA
TR1	PNP	_	_	-
TR2	PNP			_
R1	bias resistor	47	-	kΩ
R2	bias resistor	47		kO

PARAMETER

QUICK REFERENCE DATA

SYMBOL

DESCRIPTION

PNP/PNP resistor-equipped transistors (see "Simplified outline, symbol and pinning" for package details).

PRODUCT OVERVIEW

TYPE NUMBER	PAC	(AGE	MARKING CODE	NPN/PNP	NPN/NPN	
TIPE NOWIBER	PHILIPS	EIAJ	WARKING CODE	COMPLEMENT	COMPLEMENT	
PEMB2	SOT666	-	B2	PEMD12	PEMH2	
PUMB2	SOT363	SC-88	B*2 ⁽¹⁾	PUMD12	PUMH2	

Note

- 1. * = p: Made in Hong Kong.
 - * = t: Made in Malaysia.
 - * = W: Made in China.

SIMPLIFIED OUTLINE, SYMBOL AND PINNING

TYPE NUMBER	SIMPLIFIED OUTLINE AND SYMBOL	PINNING		
ITPE NUMBER	SIMPLIFIED OUTLINE AND STMBOL	PIN	DESCRIPTION	
PEMB2	6 5 4	1	emitter TR1	
PUMB2	6 5 4	2	base TR1	
	R1 R2	3	collector TR2	
	TR2	4	emitter TR2	
	TR1	5	base TR2	
	$\left[\begin{array}{c c} & R2 \\ \hline \end{array}\right]$ R2 R1	6	collector TR1	
	1 2 3			
	1 2 3 Top view MAM477			
	input			

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PEMB2; PUMB2

ORDERING INFORMATION

TYPE NUMBER		PACKAGE	
ITPE NUMBER	NAME	DESCRIPTION	VERSION
PEMB2	_	plastic surface mounted package; 6 leads	SOT666
PUMB2	1	plastic surface mounted package; 6 leads	SOT363

LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
Per transis	stor			•	
V _{CBO}	collector-base voltage	open emitter	-	-50	V
V _{CEO}	collector-emitter voltage	open base	-	-50	V
V _{EBO}	emitter-base voltage	open collector	_	-5	V
VI	input voltage				
	positive		_	+10	V
	negative		_	-40	V
Io	output current (DC)		_	-100	mA
I _{CM}	peak collector current	-		-100	mA
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C			
	SOT363	note 1	_	200	mW
	SOT666	notes 1 and 2	_	200	mW
T _{stg}	storage temperature		-65	+150	°C
Tj	junction temperature		-	150	°C
T _{amb}	operating ambient temperature		-65	+150	°C
Per device	•				
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C			
	SOT363	note 1	_	300	mW
	SOT666	notes 1 and 2	_	300	mW

Notes

- 1. Device mounted on an FR4 printed-circuit board, single-sided copper, standard footprint.
- 2. Reflow soldering is the only recommended soldering method.

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THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
Per transist	or			
R _{th j-a} thermal resistance from junction to ambi		T _{amb} ≤ 25 °C		
	SOT363	note 1	625	K/W
	SOT666	notes 1 and 2	625	K/W
Per device				
R _{th j-a} thermal resistance from junction to an		T _{amb} ≤ 25 °C		
	SOT363	note 1	416	K/W
	SOT666	note 1	416	K/W

Notes

- 1. Device mounted on an FR4 printed-circuit board, single-sided copper, standard footprint.
- 2. Reflow soldering is the only recommended soldering method.

CHARACTERISTICS

 T_{amb} = 25 °C unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
I _{CBO}	collector-base cut-off current	$V_{CB} = -50 \text{ V}; I_E = 0$	-	_	-100	nA
I _{CEO}	collector-emitter cut-off current	$V_{CE} = -30 \text{ V}; I_B = 0$	_	_	-1	μΑ
		$V_{CE} = -30 \text{ V}; I_{B} = 0; T_{j} = 150 ^{\circ}\text{C}$	_	_	-50	μΑ
I _{EBO}	emitter-base cut-off current	$V_{EB} = -5 \text{ V}; I_C = 0$	_	_	-90	μΑ
h _{FE}	DC current gain	$V_{CE} = -5 \text{ V}; I_{C} = -5 \text{ mA}$	80	_	_	
V _{CEsat}	saturation voltage	$I_C = -10 \text{ mA}; I_B = -0.5 \text{ mA}$	_	_	-150	mV
$V_{i(off)}$	input-off voltage	$V_{CE} = -5 \text{ V; } I_{C} = -100 \mu\text{A}$	-	-1.2	-0.8	V
$V_{i(on)}$	input-on voltage	$V_{CE} = -0.3 \text{ V}; I_{C} = -2 \text{ mA}$	-3	-1.6	_	V
R1	input resistor		33	47	61	kΩ
<u>R2</u> R1	resistor ratio		0.8	1	1.2	
C _c	collector capacitance	$I_E = i_e = 0$; $V_{CB} = -10 \text{ V}$; $f = 1 \text{ MHz}$	_	_	3	pF

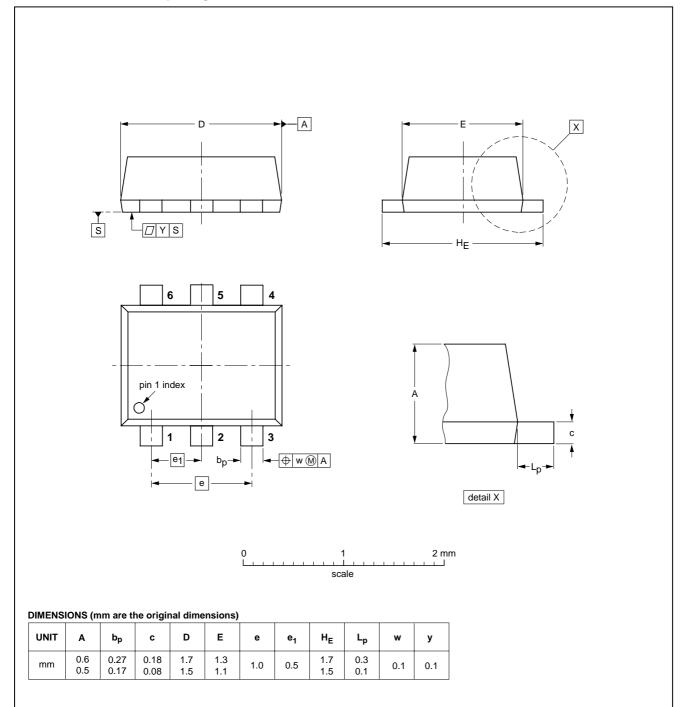
PNP/PNP resistor-equipped transistors; R1 = 47 k Ω , R2 = 47 k Ω

PEMB2; PUMB2

PACKAGE OUTLINES

Plastic surface mounted package; 6 leads

SOT666



REFERENCES

EIAJ

JEDEC

EUROPEAN

PROJECTION

ISSUE DATE

01-01-04 01-08-27

2003 Oct 15 5

IEC

OUTLINE VERSION

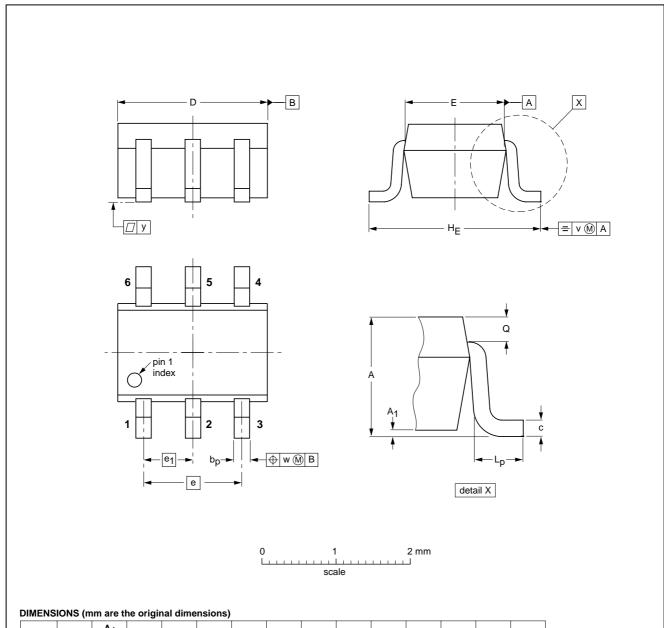
SOT666

PNP/PNP resistor-equipped transistors; R1 = 47 k Ω , R2 = 47 k Ω

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Plastic surface mounted package; 6 leads

SOT363



UNI	- A	A ₁ max	bp	С	D	E	е	e ₁	HE	Lp	Q	v	w	у
mm	1.1 0.8	0.1	0.30 0.20	0.25 0.10	2.2 1.8	1.35 1.15	1.3	0.65	2.2 2.0	0.45 0.15	0.25 0.15	0.2	0.2	0.1

OUTLINE		REFER	RENCES	EUROPEAN	ISSUE DATE	
VERSION	IEC	JEDEC	EIAJ	PROJECTION	ISSUE DATE	
SOT363			SC-88		97-02-28	

PNP/PNP resistor-equipped transistors; R1 = 47 k Ω , R2 = 47 k Ω

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DATA SHEET STATUS

DOCUMENT STATUS ⁽¹⁾	PRODUCT STATUS ⁽²⁾	DEFINITION
Objective data sheet	Development	This document contains data from the objective specification for product development.
Preliminary data sheet	Qualification	This document contains data from the preliminary specification.
Product data sheet	Production	This document contains the product specification.

Notes

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